AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A method for producing a semiconductor device comprising:

forming wiring by ejecting a first solution comprising a conductive material using a first solution ejector having solution ejection ports arranged in a cluster-pattern with moving the first solution ejector,

forming a resist mask by ejecting a second solution comprising a resist material on the wiring using a second solution ejector having solution ejection ports arranged in a cluster-pattern with moving the second solution ejector, and

etching the wiring using an atmospheric-pressure plasma device having a linear plasma generator using the resist mask as a mask by generating plasma between a first electrode of the linear plasma generator and a second electrode surrounding the first electrode of the linear plasma generator,

wherein at least the first electrode has a sheet-like shape.

2. (Canceled)

3. (Currently Amended) A method for producing a semiconductor device comprising:

forming wiring,

forming a resist mask at least on the wiring by ejecting a solution comprising a resist material using a solution ejector having solution ejection ports arranged in a cluster-pattern with moving the solution ejector, and

etching the wiring using an atmospheric-pressure plasma device having a linear plasma generator using the resist mask as a mask by generating plasma between a first electrode of the linear plasma generator and a second electrode surrounding the first electrode of the linear plasma generator,

wherein at least the first electrode has a sheet-like shape.

4. (Canceled)

5. (Previously Presented) The method for producing the semiconductor device in claim 1, wherein when the first solution is ejected using the first solution ejector, a substrate is heated.

6. (Previously Presented) The method for producing the semiconductor device in any one of claim 1 and claim 3, wherein the etching and/or ashing are/is processed at the atmospheric pressure or near-atmospheric pressure.

7. (Withdrawn) A method for producing a display device using a semiconductor device comprising:

forming wiring using a first solution ejector for ejecting a conductive material,

forming a resist mask on the wiring using a second solution ejector, and

etching the wiring using an atmospheric-pressure plasma device having a linear plasma generator using the resist mask as a mask.

8. (Withdrawn) A method for producing a display device using a semiconductor device comprising:

forming wiring using a solution ejector for ejecting a conductive material,

forming a resist mask at least on the wiring, and

etching the wiring using an atmospheric-pressure plasma device having a linear plasma generator using the resist mask as a mask.

9. (Withdrawn) A method for producing a display device using a semiconductor device comprising:

forming wiring,

forming a resist mask at least on the wiring using a solution ejector, and

etching the wiring using an atmospheric-pressure plasma device having a linear

plasma generator using the resist mask as a mask.

10. (Withdrawn) The method for producing the display device using the semiconductor device in any one of claim 7 to claim 9, wherein the solution ejector has one or more of solution ejection ports.

11. (Withdrawn) The method for producing the display device using the semiconductor device in any one of claim 7 to claim 9, wherein when a solution is ejected using the solution ejector, a substrate is heated.

12. (Withdrawn) The method for producing the display device using the semiconductor device in any one of claim 7 to claim 8, wherein the etching and/or the ashing are/is processed at the atmospheric pressure or near-atmospheric pressure.

13. (Currently Amended) A method for producing a semiconductor device comprising:

forming wiring by ejecting a first solution comprising a conductive material using a first solution ejector having solution ejection ports arranged in a cluster-pattern with moving the first solution ejector,

forming a resist mask by ejecting a second solution comprising a resist material on the wiring using a second solution ejector having solution ejection ports arranged in a cluster-pattern with moving the second solution ejector, and

etching the wiring using an atmospheric-pressure plasma device having a plurality of linearly-arranged plasma generators using the resist mask as a mask by generating plasma between a first electrode of the linear plasma generator and a second electrode surrounding the first electrode of each of the plurality of linearly-arranged plasma generators,

wherein each of the first solution ejector and the second solution ejector has three ejection ports forming a triangle.

14. (Currently Amended) A method for producing a semiconductor device comprising:

forming wiring by ejecting a solution comprising a conductive material using a solution ejector having solution ejection ports arranged in a cluster-pattern with moving the solution ejector,

forming a resist mask at least on the wiring, and

etching the wiring using an atmospheric-pressure plasma device having a plurality of linearly-arranged plasma generators using the resist mask as a mask by generating plasma between a first electrode of the linear plasma generator and a second electrode surrounding the first electrode of each of the plurality of linearly-arranged plasma generators,

wherein the solution ejector has three ejection ports forming a triangle.

15. (Currently Amended) A method for producing a semiconductor device comprising:

forming wiring,

forming a resist mask at least on the wiring by ejecting a solution comprising a resist material using a solution ejector having solution ejection ports arranged in a cluster-pattern with moving the solution ejector, and

etching the wiring using an atmospheric-pressure plasma device having a plurality of linearly-arranged plasma generators using the resist mask as a mask by generating plasma between a first electrode of the linear plasma generator and a second electrode surrounding the first electrode of each of the plurality of linearly-arranged plasma generators,

wherein the solution ejector has three ejection ports forming a triangle.

16. (Canceled)

17. (Previously Presented) The method for producing the semiconductor device in claim 13, wherein when the first solution is ejected using the first solution ejector, a substrate is heated.

18. (Previously presented) The method for producing the semiconductor device in any one of claim 13 to claim 15, wherein the etching is processed at the atmospheric pressure or near-atmospheric pressure.

19. (Withdrawn) A method for producing a display device using a semiconductor device comprising:

forming wiring using a first solution ejector for ejecting a conductive material,

forming a resist mask on the wiring using a second solution ejector, and

etching the wiring using an atmospheric-pressure plasma device having a plurality of linearly-arranged plasma generators using the resist mask as a mask.

20. (Withdrawn) A method for producing a display device using a semiconductor device comprising:

forming wiring using a solution ejector for ejecting a conductive material,

forming a resist mask at least on the wiring, and

etching the wiring using an atmospheric-pressure plasma device having a plurality of linearly-arranged plasma generators using the resist mask as a mask.

21. (Withdrawn) A method for producing a display device using a semiconductor device comprising:

forming wiring,

forming a resist mask at least on the wiring using a solution ejector, and

etching the wiring using an atmospheric-pressure plasma device having a plurality of linearly-arranged plasma generators using the resist mask as a mask.

22. (Withdrawn) A method for producing the display device using the semiconductor device in any one of claim 19 to claim 21, wherein the solution ejector has one or more of solution ejection ports.

23. (Withdrawn) A method for producing the display device using the semiconductor device in any one of claim 19 to claim 21, wherein when a solution is ejected using the solution ejector, a substrate is heated.

24. (Withdrawn) A method for producing the display device using the semiconductor device in any one of claim 19 to claim 21, wherein the etching is processed at the atmospheric pressure or near-atmospheric pressure.

25. (Canceled)

26. (Canceled)

27. (Previously Presented) The method for producing the semiconductor device in claim 1, wherein when the second solution is ejected using the second solution ejector, a substrate is heated.

28. (Previously Presented) The method for producing the semiconductor device in claim 3, wherein when the solution is ejected using the solution ejector, a substrate is heated.

29. (Canceled)

30. (Canceled)

31. (Previously Presented) The method for producing the semiconductor device in claim 13, wherein when the second solution is ejected using the second solution ejector, a substrate is heated.

32. (Previously Presented) The method for producing the semiconductor device in claim 14 or 15, wherein when the solution is ejected using the solution ejector, a substrate is heated.

33. (Previously Presented) The method for producing the semiconductor device in claim 1, wherein each of the first solution ejector and the second solution ejector has three ejection ports forming a triangle.

34. (Previously Presented) The method for producing the semiconductor device in claim 3, wherein the solution ejector has three ejection ports forming a triangle.

35. (Canceled)

36. (Canceled)

37. (Canceled)